

April 2015

H11AV1M, H11AV1AM 6-Pin DIP Phototransistor Optocouplers

Features

- H11AV1M and H11AV1AM Feature 0.3" and 0.4" Input-Output Lead Spacing Respectively
- Safety and Regulatory Approvals:
 - UL1577, 4,170 VAC_{RMS} for 1 Minute
 - DIN-EN/IEC60747-5-5, 850 V Peak Working Insulation Voltage

DescriptionThe general pur

The general purpose optocouplers consist of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 6-pin dual in-line white package.

Applications

- Power Supply Regulators
- Digital Logic Inputs
- Microprocessor Inputs

Schematic

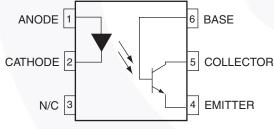


Figure 1. Schematic

Package Outlines

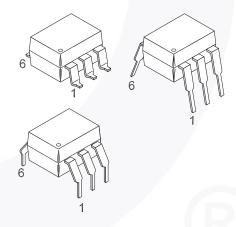


Figure 2. Package Outlines

Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
Installation Classifications per DIN VDE	< 150 V _{RMS}	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V _{RMS}	I–IV
Climatic Classification		55/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V	Input-to-Output Test Voltage, Method A, V_{IORM} x 1.6 = V_{PR} , Type and Sample Test with t_{m} = 10 s, Partial Discharge < 5 pC	1360	V _{peak}
V PR	Input-to-Output Test Voltage, Method B, V _{IORM} x 1.875 = V _{PR} , 100% Production Test with t _m = 1 s, Partial Discharge < 5 pC		V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	850	V _{peak}
V _{IOTM}	Highest Allowable Over-Voltage	6000	V _{peak}
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
	External Clearance (for Option TV, 0.4" Lead Spacing)	≥ 10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.5	mm
T _S	Case Temperature ⁽¹⁾	175	°C
I _{S,INPUT}	Input Current ⁽¹⁾	350	mA
P _{S,OUTPUT}	Output Power ⁽¹⁾	800	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V ⁽¹⁾	> 10 ⁹	Ω

Note:

1. Safety limit values – maximum values allowed in the event of a failure.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Value	Unit
TOTAL DEV	ICE	-	
T _{STG}	Storage Temperature	-40 to +125	°C
T _{OPR}	Operating Temperature	-40 to +100	°C
T _J	Junction Temperature	-40 to +125	°C
T _{SOL}	Lead Solder Temperature	260 for 10 seconds	°C
Б	Total Device Power Dissipation @ T _A = 25°C	270	mW
P_{D}	Derate Above 25°C	2.94	mW/°C
EMITTER			
I _F	DC / Average Forward Input Current	60	mA
V _R	Reverse Input Voltage	6	V
Ь	LED Power Dissipation @ T _A = 25°C	120	mW
P_{D}	Derate Above 25°C	1.41	mW/°C
DETECTOR		· · · · · · · · · · · · · · · · · · ·	
V_{CEO}	Collector-to-Emitter Voltage	70	V
V_{CBO}	Collector-to-Base Voltage	70	V
V _{ECO}	Emitter-to-Collector Voltage	7	V
	Detector Power Dissipation @ T _A = 25°C	150	mW
P_{D}	Derate Above 25°C	1.76	mW/°C

Electrical Characteristics

 $T_A = 25$ °C unless otherwise specified.

Individual Component Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
EMITTER						
		T _A = 25°C	0.80	1.18	1.50	
V _F	Input Forward Voltage (I _F = 10 mA)	T _A = -55°C	0.90	1.28	1.70	V
		T _A = 100°C	0.70	1.05	1.40	
I _R	Reverse Leakage Current	V _R = 6.0 V			10	μA
DETECTOR			•	•		
BV _{CEO}	Collector-to-Emitter Breakdown Voltage	I _C = 1.0 mA, I _F = 0	70	100		V
BV _{CBO}	Collector-to-Base Breakdown Voltage	$I_C = 100 \mu A, I_F = 0$	70	120		V
BV _{ECO}	Emitter-to-Collector Breakdown Voltage	I _E = 100 μA, I _F = 0	7	10		V
I _{CEO}	Collector-to-Emitter Dark Current	V _{CE} = 10 V, I _F = 0		1	50	nA
I _{CBO}	Collector-to-Base Dark Current	V _{CB} = 10 V		0.5		nA
C _{CE}	Capacitance	V _{CE} = 0 V, f = 1 MHz		8		pF

Transfer Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
DC CHAR	ACTERISTIC					
CTR	Current Transfer Ratio, Collector-to-Emitter	I _F = 10 mA, V _{CE} = 10 V	100		300	%
V _{CE (SAT)}	Saturation Voltage, Collector-to-Emitter	I _C = 2 mA, I _F = 20 mA			0.4	V
AC CHARA	ACTERISTIC		•		•	
T _{ON}	Non-Saturated Turn-on Time	I_C = 2 mA, V_{CC} = 10 V, R_L = 100 Ω (Figure 13)			15	μs
T _{OFF}	Non Saturated Turn-off Time	I_C = 2 mA, V_{CC} = 10 V, R_L = 100 Ω (Figure 13)			15	μs

Isolation Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V _{ISO}	Input-Output Isolation Voltage	t = 1 Minute	4170			VAC _{RMS}
C _{ISO}	Isolation Capacitance	V _{I-O} = 0 V, f = 1 MHz		0.2		pF
R _{ISO}	Isolation Resistance	V _{I-O} = ±500 VDC, T _A = 25°C	10 ¹¹			Ω

Typical Performance Curves

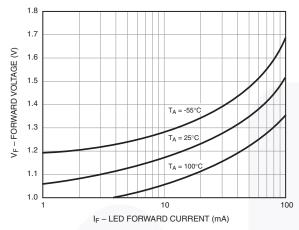


Figure 3. LED Forward Voltage vs. Forward Current

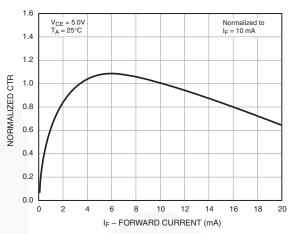


Figure 4. Normalized CTR vs. Forward Current

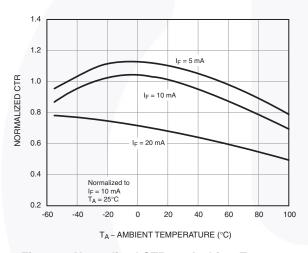


Figure 5. Normalized CTR vs. Ambient Temperature

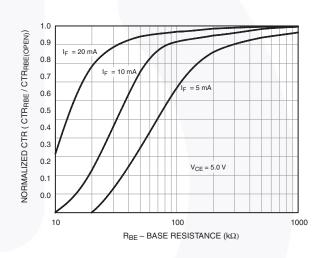


Figure 6. CTR vs. RBE (Unsaturated)

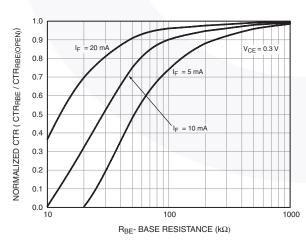


Figure 7. CTR vs. RBE (Saturated)

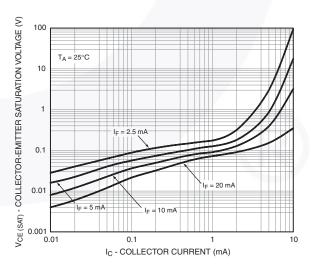


Figure 8. Collector-Emitter Saturation Voltage vs. Collector Current

Typical Performance Curves (Continued)

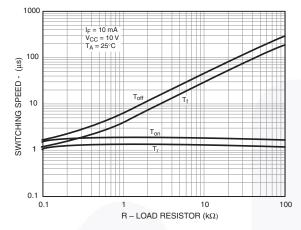


Figure 9. Switching Speed vs. Load Resistor

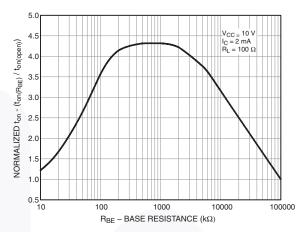


Figure 10. Normalized ton vs. RBE

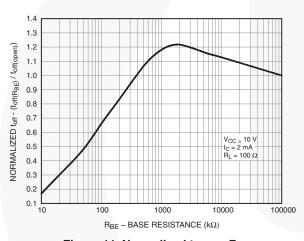


Figure 11. Normalized toff vs. RBE

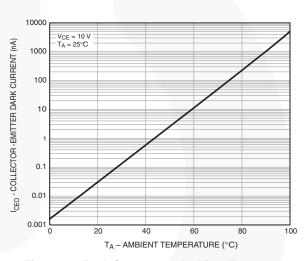


Figure 12. Dark Current vs. Ambient Temperature

Switching Time Test Circuit and Waveform

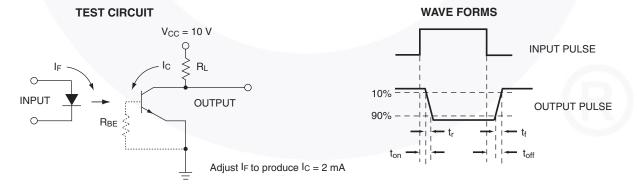


Figure 13. Switching Time Test Circuit and Waveform

Reflow Profile

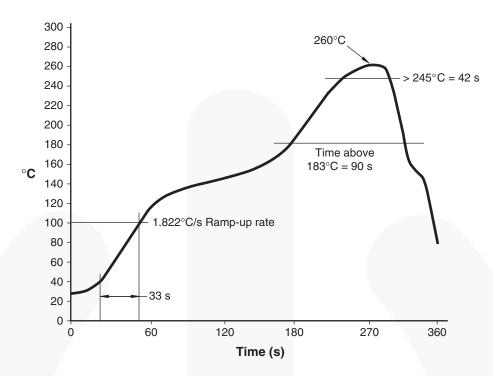


Figure 14. Reflow Profile

Ordering Information

Part Number	Package	Packing Method
H11AV1M	DIP 6-Pin	Tube (50 Units)
H11AV1SM	SMT 6-Pin (Lead Bend)	Tube (50 Units)
H11AV1SR2M	SMT 6-Pin (Lead Bend)	Tape and Reel (1000 Units)
H11AV1VM	DIP 6-Pin, DIN EN/IEC60747-5-5 Option	Tube (50 Units)
H11AV1SVM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tube (50 Units)
H11AV1SR2VM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tape and Reel (1000 Units)
H11AV1AM	DIP 6-Pin, 0.4" Lead Spacing	Tube (50 Units)
H11AV1AVM	DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option	Tube (50 Units)

Marking Information

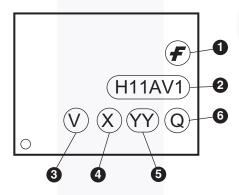


Figure 15. Top Mark

Table 1. Top Mark Definitions

1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., "5"
5	Digit Work Week, Ranging from "01" to "53"
6	Assembly Package Code







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